

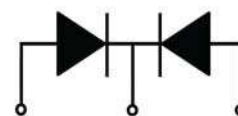
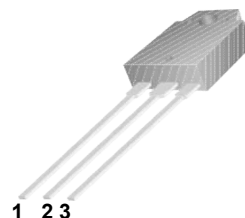
## MUR2060PT

## Features:

- High Surge Capability
- Low Forward Voltage Drop
- High Current Capability
- Super Fast Switching Speed For High Efficiency



TO-3P



1. Anode 2. Cathode 3. Anode

## Absolute Maximum Ratings (Ta=25°C unless otherwise noted)

Rating	Symbol	MUR2060PT	Unit
Maximum Repetitive Voltage	VRRM	600	V
DC Blocking Voltage	VDC	600	V
Maximum Average Forward Current	I <sub>AV</sub>	20	A
Peak Forward Surge Current, 8.3ms single half sine-wave superimposed on rated load (JEDEC method)	I <sub>FSM</sub>	200	A
Maximum Forward Voltage at 10A, per element	V <sub>F</sub>	2.4	V
Maximum DC Reverse Current at TA=25 °C	I <sub>R</sub>	50	μA
Rated DC Blocking Voltage TA=100°C		200	
Maximum Reverse Recovery Time (Note 1)	TRR	30	ns
Maximum Thermal Resistance (Note 2)	R <sub>θ-jc</sub>	3.0	°C/W
Operating Junction and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-50~+150	°C

## NOTES:

1. Reverse Recovery Test Conditions: I<sub>F</sub>=0.5A, I<sub>R</sub>=1A, I<sub>rr</sub>=0.25A.
2. Thermal resistance from junction to case.

Typical Characteristics

FIG. 1 - FORWARD CURRENT DERATING CURVE

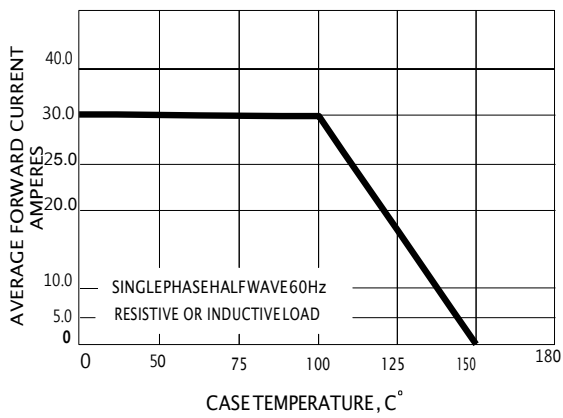


FIG. 2 - MAXIMUM NON-REPETITIVE SURGE CURRENT

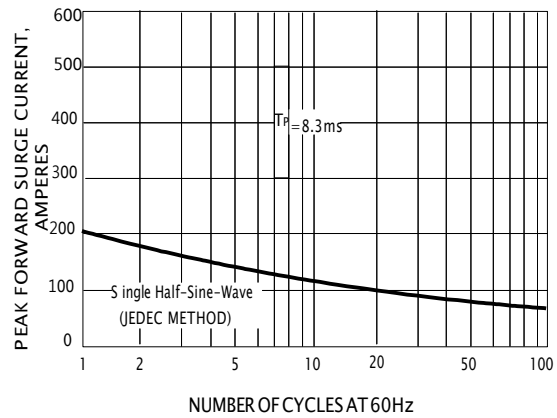


FIG. 3 - TYPICAL REVERSE CHARACTERISTICS

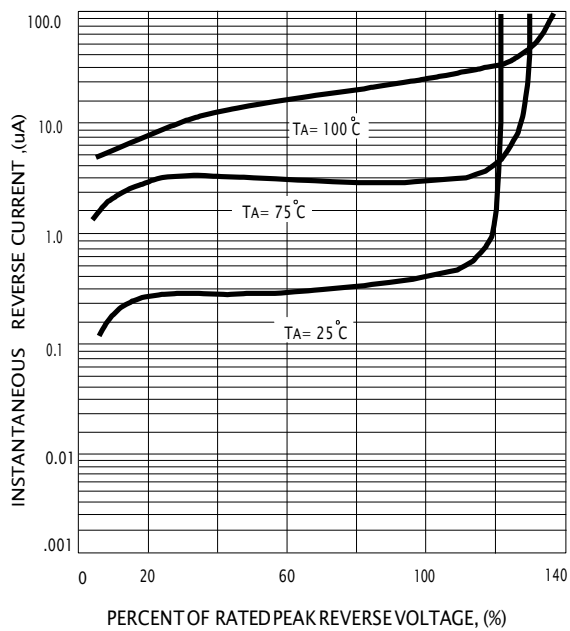
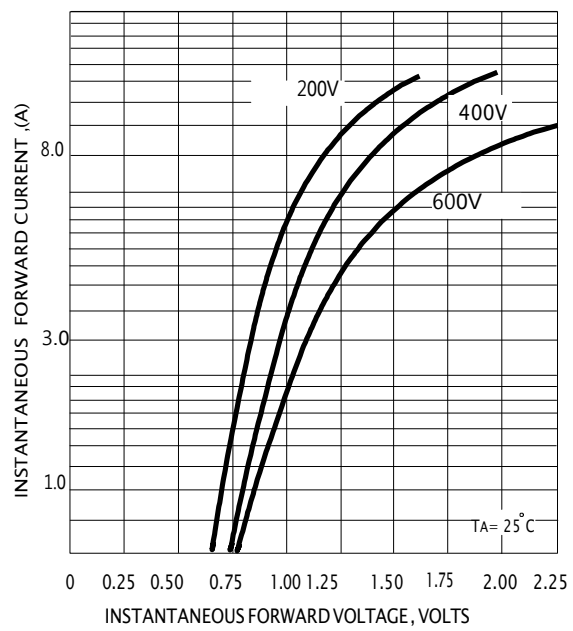


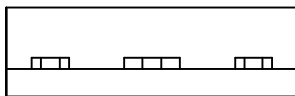
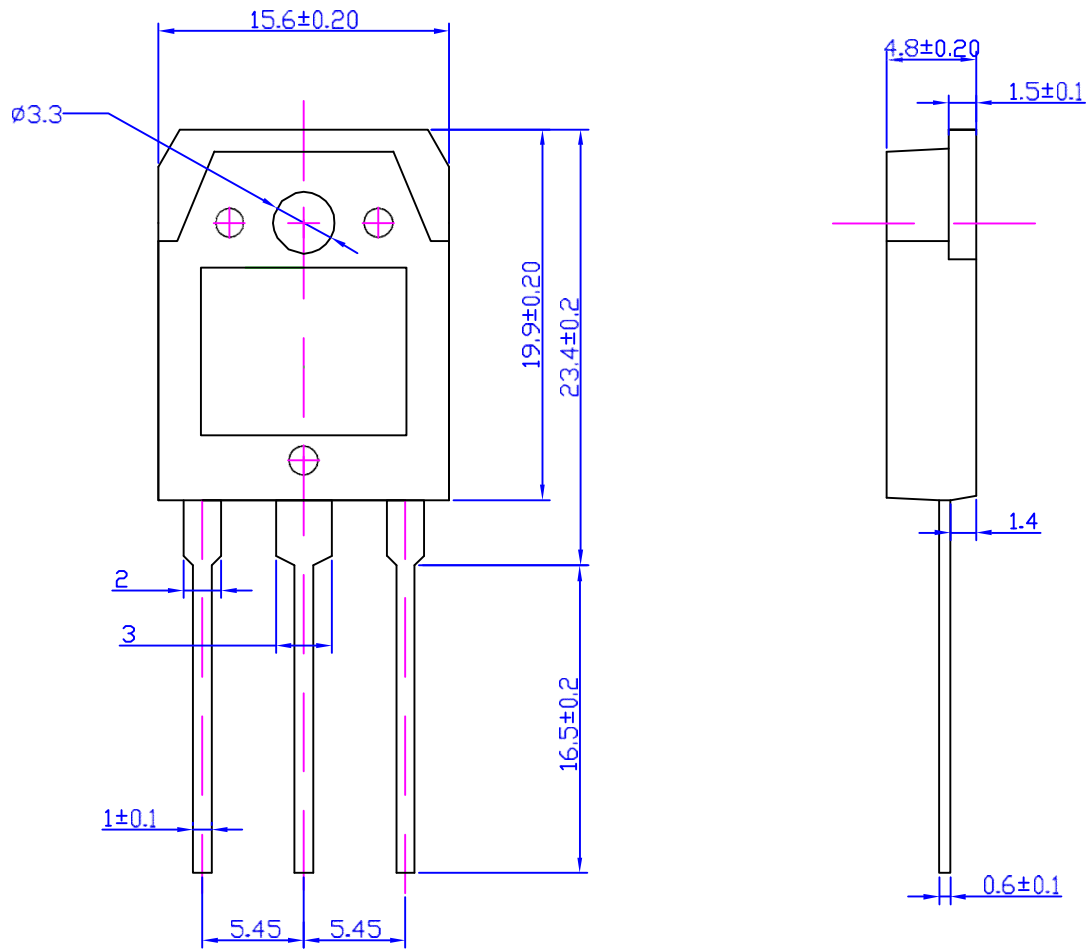
FIG. 4 - TYPICAL FORWARD CHARACTERISTICS



## Package Dimension

## TO-3P

Units: mm



## 技术要求:

- 1 未标注面要求要求成型后表面 $R_a=0.2$
- 2 未注明公差要求 $\pm 0.15$ mm
- 3 树脂体不准有缺损, 缩孔, 裂纹, 气泡等有害缺陷